PSMN013-100PS

N-channel 100V 13.9mΩ standard level MOSFET in TO220.

10 August 2012 Product data sheet

1. Product profile

1.1 General description

Standard level N-channel MOSFET in TO220 package qualified to 175C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Improved dynamic avalanche performance
- Suitable for standard level gate drive

1.3 Applications

- DC-to-DC converters
- Load switching
- Motor control
- Server power supplies

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
V_{DS}	drain-source voltage	$T_j \geq 25$ °C; $T_j \leq 175$ °C		-	-	100	V
I_D	drain current	T_{mb} = 25 °C; V_{GS} = 10 V; Fig. 1	[1]	-	-	68	A
P_{tot}	total power dissipation	T_{mb} = 25 °C; Fig. 2		-	-	170	W
T_j	junction temperature			-55	-	175	°C
Static characteristics							
R_{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 15 A; T_j = 100 °C; Fig. 12		-	19.4	25	mΩ
		V_{GS} = 10 V; I_D = 15 A; T_j = 25 °C; Fig. 13	[2]	-	10.8	13.9	mΩ
Dynamic characteristics							
Q_{GD}	gate-drain charge	V_{GS} = 10 V; I_D = 25 A; V_{DS} = 50 V; Fig. 15; Fig. 14		-	17	-	nC

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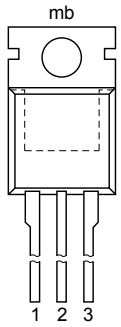
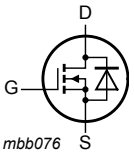
Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$Q_{G(tot)}$	total gate charge	V_{GS} = 10 V; I_D = 25 A; V_{DS} = 50 V; Fig. 14; Fig. 15		-	59	-	nC
Avalanche ruggedness							
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 68 A; V_{sup} ≤ 100 V; unclamped; R_{GS} = 50 Ω		-	-	128	mJ

[1] Continuous current is limited by package
[2] Measured 3 mm from package.

2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	 TO-220AB (SOT78)	
2	D	drain		
3	S	source		
mb	D	mounting base; connected to drain		

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN013-100PS	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78

4. Marking

Table 4. Marking codes

Type number	Marking code
PSMN013-100PS	PSMN013-100PS

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5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	$T_j \geq 25$ °C; $T_j \leq 175$ °C		-	100	V
V_{DGR}	drain-gate voltage	$T_j \leq 175$ °C; $T_j \geq 25$ °C; $R_{GS} = 20$ kΩ		-	100	V
V_{GS}	gate-source voltage			-20	20	V
I_D	drain current	$V_{GS} = 10$ V; $T_{mb} = 100$ °C; Fig. 1	[1]	-	47	A
		$V_{GS} = 10$ V; $T_{mb} = 25$ °C; Fig. 1	[1]	-	68	A
I_{DM}	peak drain current	pulsed; $t_p \leq 10$ µs; $T_{mb} = 25$ °C; Fig. 3		-	272	A
P_{tot}	total power dissipation	$T_{mb} = 25$ °C; Fig. 2		-	170	W
T_{stg}	storage temperature			-55	175	°C
T_j	junction temperature			-55	175	°C
$T_{sld(M)}$	peak soldering temperature			-	260	°C
Source-drain diode						
I_S	source current	$T_{mb} = 25$ °C	[1]	-	68	A
I_{SM}	peak source current	pulsed; $t_p \leq 10$ µs; $T_{mb} = 25$ °C		-	272	A
Avalanche ruggedness						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$V_{GS} = 10$ V; $T_{j(init)} = 25$ °C; $I_D = 68$ A; $V_{sup} \leq 100$ V; unclamped; $R_{GS} = 50$ Ω		-	128	mJ

[1] Continuous current is limited by package

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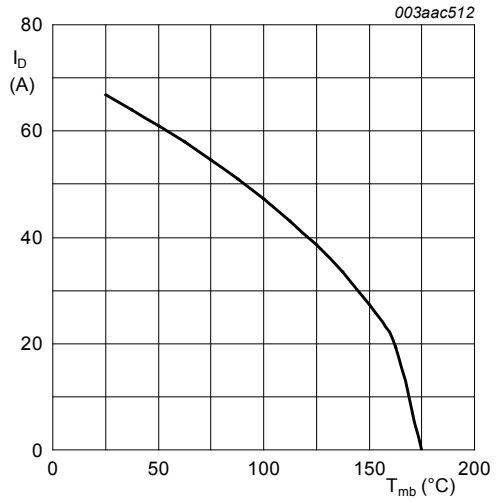

Fig. 1. Continuous drain current as a function of mounting base temperature

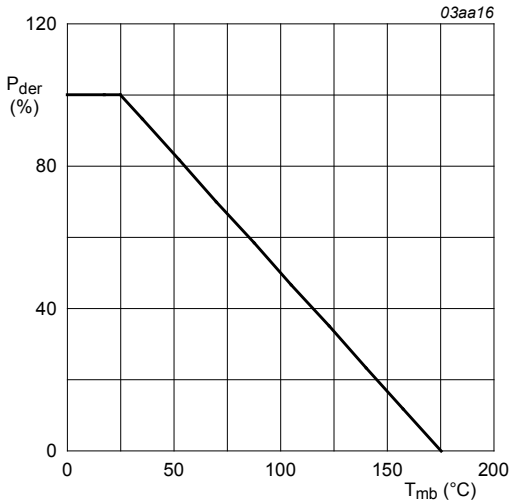

Fig. 2. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25°C)}} \times 100\ \%$$

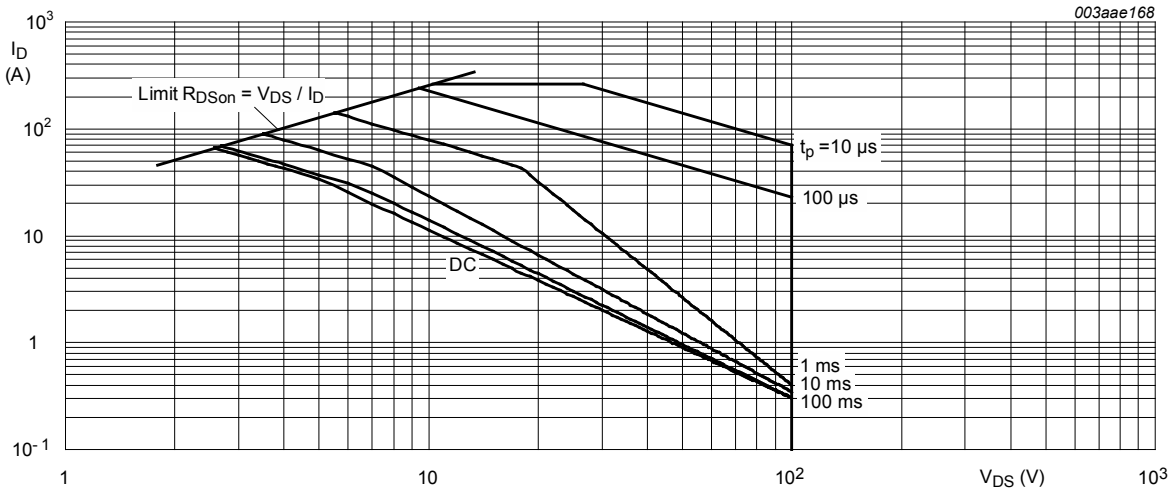

Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

$T_{mb} = 25\ °C$; I_{DM} is a single pulse

6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	Fig. 4		-	0.5	0.9	K/W

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Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	vertical in free air		-	60	-	K/W

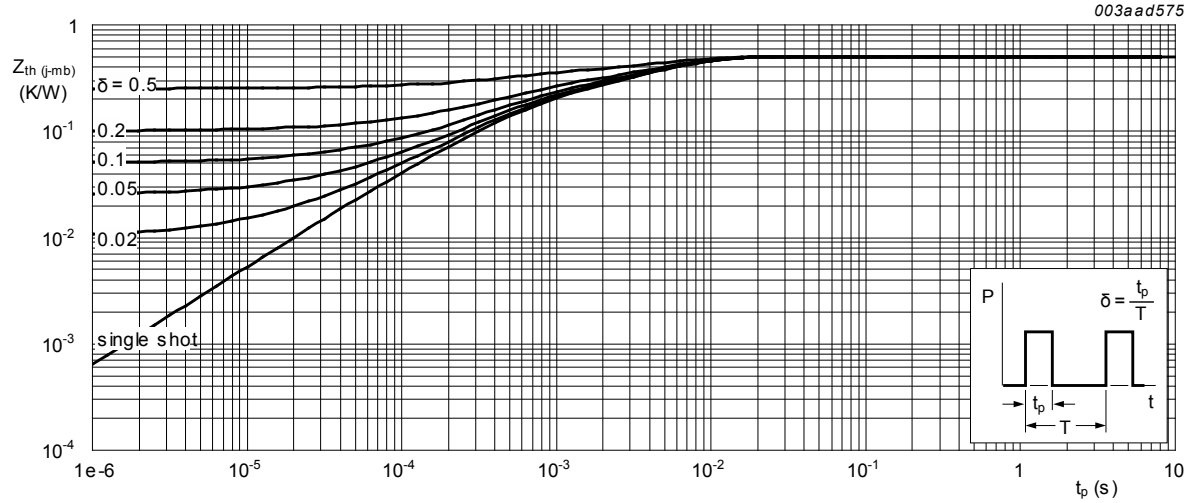

Fig. 4. Transient thermal impedance from junction to mounting base as a function of pulse duration; typical values

7. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Static characteristics							
$V_{(BR)DSS}$	drain-source breakdown voltage	I_D = 0.25 mA; V_{GS} = 0 V; T_j = -55 °C		90	-	-	V
		I_D = 0.25 mA; V_{GS} = 0 V; T_j = 25 °C		100	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	I_D = 1 mA; V_{DS} = V_{GS}; T_j = 175 °C; Fig. 10		1	-	-	V
		I_D = 1 mA; V_{DS} = V_{GS}; T_j = 25 °C; Fig. 10; Fig. 11		2	3	4	V
		I_D = 1 mA; V_{DS} = V_{GS}; T_j = -55 °C; Fig. 10		-	-	4.6	V
I_{DSS}	drain leakage current	V_{DS} = 100 V; V_{GS} = 0 V; T_j = 125 °C		-	-	100	μA
		V_{DS} = 100 V; V_{GS} = 0 V; T_j = 25 °C		-	0.06	2	μA
I_{GSS}	gate leakage current	V_{GS} = 20 V; V_{DS} = 0 V; T_j = 25 °C		-	10	100	nA
		V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 °C		-	10	100	nA
R_{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 15 A; T_j = 100 °C; Fig. 12		-	19.4	25	mΩ

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Symbol	Parameter	Conditions		Min	Typ	Max	Unit
		V_{GS} = 10 V; I_D = 15 A; T_j = 175 °C; Fig. 12		-	29.5	38.9	mΩ
		V_{GS} = 10 V; I_D = 15 A; T_j = 25 °C; Fig. 13	[1]	-	10.8	13.9	mΩ
R_G	internal gate resistance (AC)	f = 1 MHz		-	1	-	Ω
Dynamic characteristics							
$Q_{G(tot)}$	total gate charge	I_D = 25 A; V_{DS} = 50 V; V_{GS} = 10 V; Fig. 14; Fig. 15		-	59	-	nC
		I_D = 0 A; V_{DS} = 0 V; V_{GS} = 10 V		-	47.6	-	nC
Q_{GS}	gate-source charge	I_D = 25 A; V_{DS} = 50 V; V_{GS} = 10 V; Fig. 14; Fig. 15		-	13.8	-	nC
$Q_{GS(th)}$	pre-threshold gate-source charge	I_D = 25 A; V_{DS} = 50 V; V_{GS} = 10 V; Fig. 15		-	9.2	-	nC
$Q_{GS(th-pl)}$	post-threshold gate-source charge			-	4.6	-	nC
Q_{GD}	gate-drain charge	I_D = 25 A; V_{DS} = 50 V; V_{GS} = 10 V; Fig. 15; Fig. 14		-	17	-	nC
$V_{GS(pl)}$	gate-source plateau voltage	V_{DS} = 50 V; Fig. 15; Fig. 14		-	4.4	-	V
C_{iss}	input capacitance	V_{DS} = 50 V; V_{GS} = 0 V; f = 1 MHz; T_j = 25 °C; Fig. 16		-	3195	-	pF
C_{oss}	output capacitance			-	221	-	pF
C_{rss}	reverse transfer capacitance			-	136	-	pF
$t_{d(on)}$	turn-on delay time	V_{DS} = 50 V; R_L = 2 Ω; V_{GS} = 10 V; $R_{G(ext)}$ = 4.7 Ω; T_j = 25 °C		-	20.7	-	ns
t_r	rise time			-	25	-	ns
$t_{d(off)}$	turn-off delay time			-	52.5	-	ns
t_f	fall time			-	24	-	ns
Source-drain diode							
V_{SD}	source-drain voltage	I_S = 15 A; V_{GS} = 0 V; T_j = 25 °C; Fig. 17		-	0.85	1.2	V
t_{rr}	reverse recovery time	I_S = 25 A; dI_S/dt = 100 A/µs; V_{GS} = 0 V; V_{DS} = 50 V		-	52	-	ns
Q_r	recovered charge			-	109	-	nC

[1] Measured 3 mm from package.

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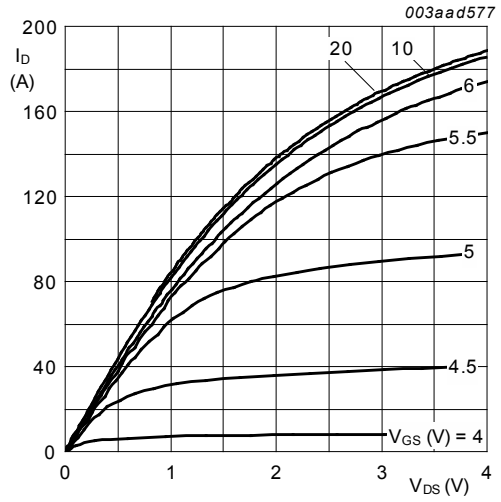

Fig. 5. Output characteristics: drain current as a function of drain-source voltage; typical values

$T_j = 25\,°C$

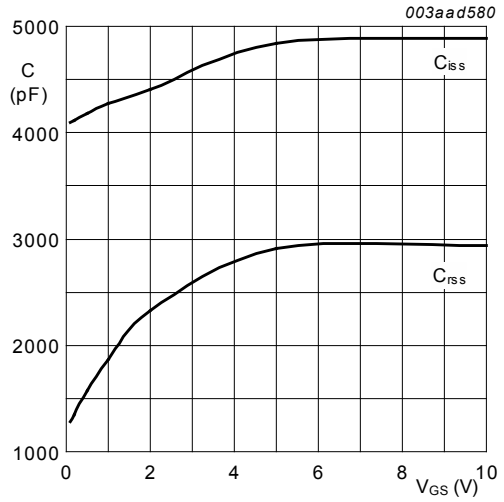

Fig. 6. Input and reverse transfer capacitances as a function of gate-source voltage; typical values

$V_{DS} = 0V; f = 1MHz$

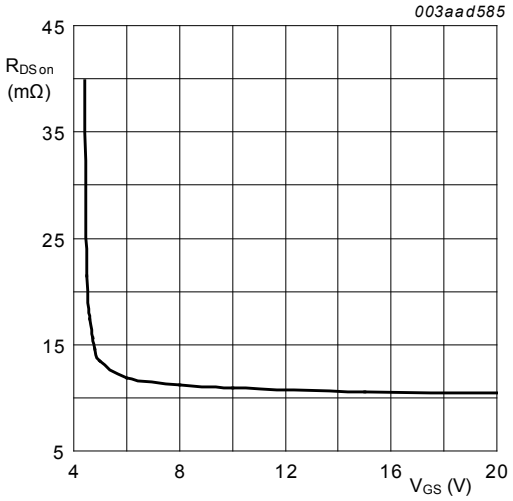

Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

$T_j = 25\,°C$

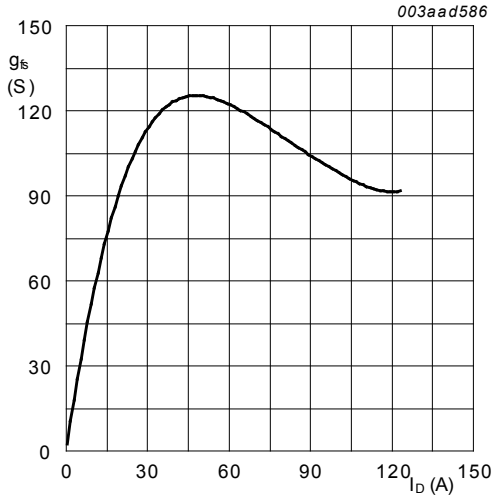

Fig. 8. Forward transconductance as a function of drain current; typical values

$T_j = 25\,°C; V_{DS} = 15V$

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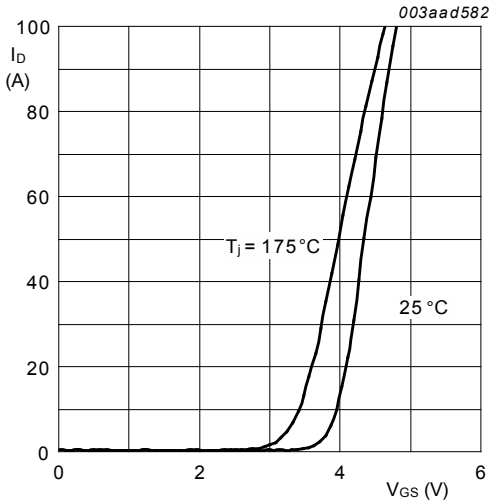

Fig. 9. Transfer characteristics: drain current as a function of gate-source voltage; typical values

$$V_{DS} > I_D \times R_{DSon}$$

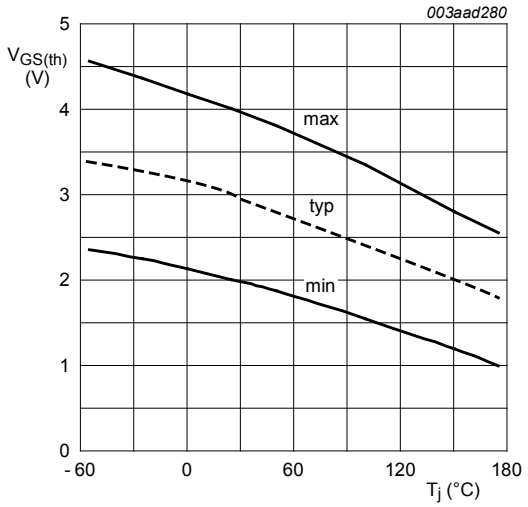

Fig. 10. Gate-source threshold voltage as a function of junction temperature

$$I_D = 1\ \text{mA};\ V_{DS} = V_{GS}$$

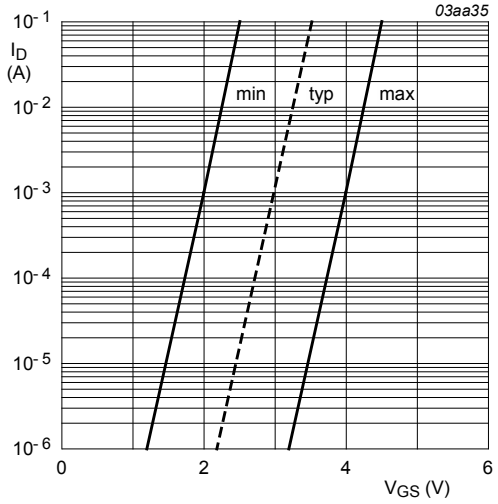

Fig. 11. Sub-threshold drain current as a function of gate-source voltage

$$T_j = 25\,°C;\ V_{DS} = 5V$$

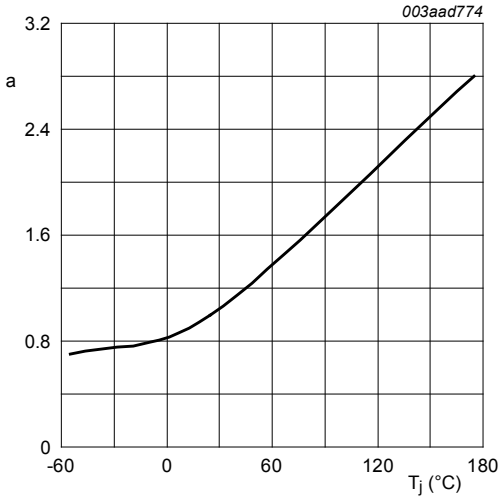

Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DSon}}{R_{DSon(25\,°C)}}$$

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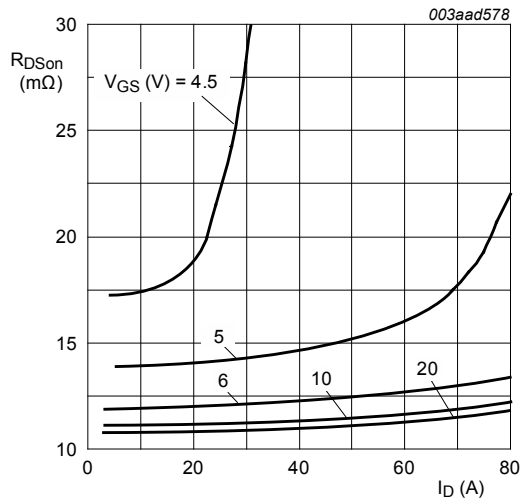

Fig. 13. Drain-source on-state resistance as a function of drain current; typical values

$T_j = 25\,°C$

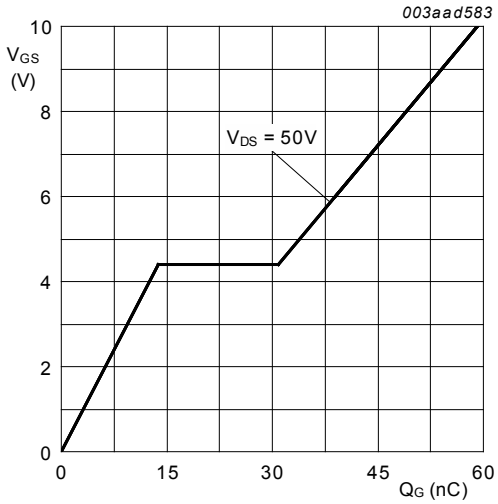

Fig. 14. Gate-source voltage as a function of gate charge; typical values

$T_j = 25\,°C; I_D = 25A$

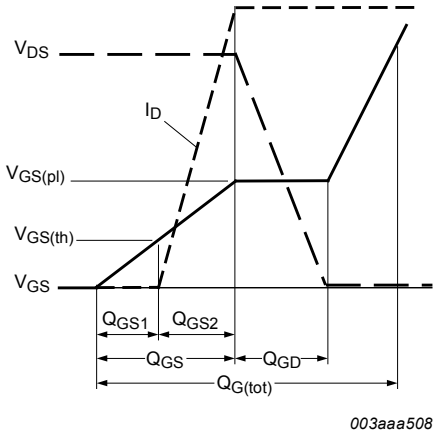

Fig. 15. Gate charge waveform definitions

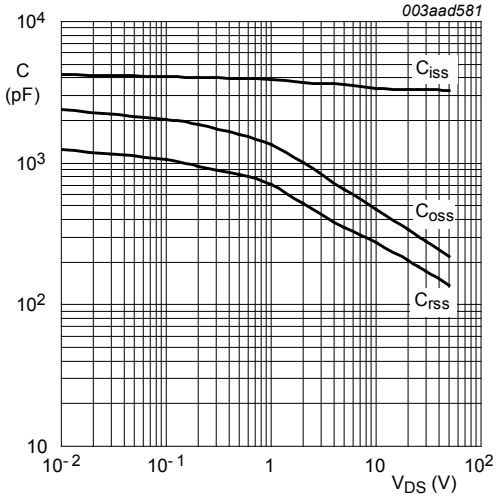

Fig. 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

$V_{GS} = 0V; f = 1MHz$

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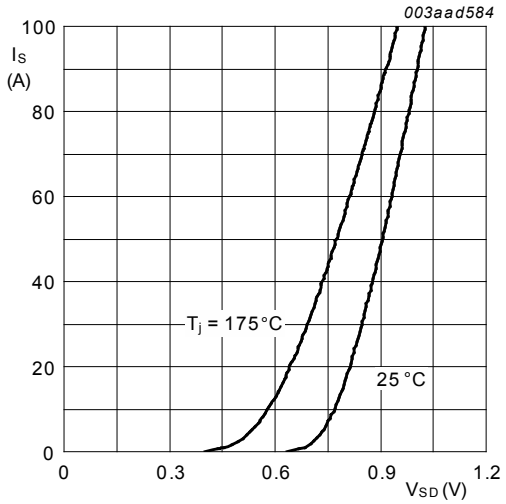

Fig. 17. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

$$V_{GS} = 0\,V$$

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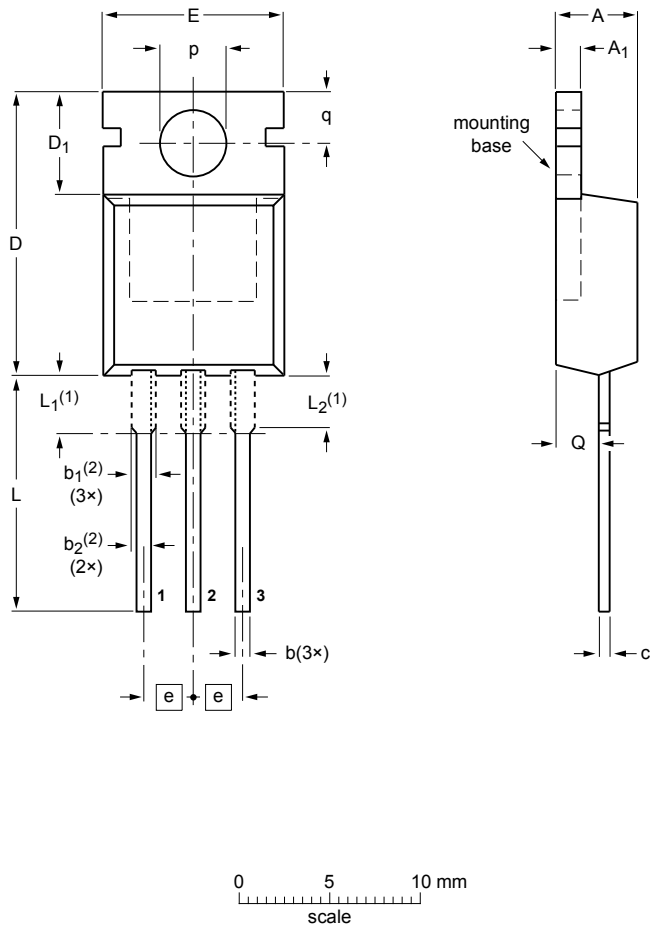
8. Package outline

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB **SOT78**



DIMENSIONS (mm are the original dimensions)

UNIT	A	A_1	b	b_1(2)	b_2(2)	c	D	D_1	E	e	L	L_1(1)	L_2(1) max.	p	q	Q
mm	4.7 4.1	1.40 1.25	0.9 0.6	1.6 1.0	1.3 1.0	0.7 0.4	16.0 15.2	6.6 5.9	10.3 9.7	2.54	15.0 12.8	3.30 2.79	3.0	3.8 3.5	3.0 2.7	2.6 2.2

Notes

1. Lead shoulder designs may vary.
2. Dimension includes excess dambar.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT78		3-lead TO-220AB	SC-46			~~08-04-23~~ 08-06-13

Fig. 18. TO-220AB (SOT78)

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9. Legal information

9.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.
[2] The term 'short data sheet' is explained in section "Definitions".
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